

Phase-out/Discontinued

2SK875

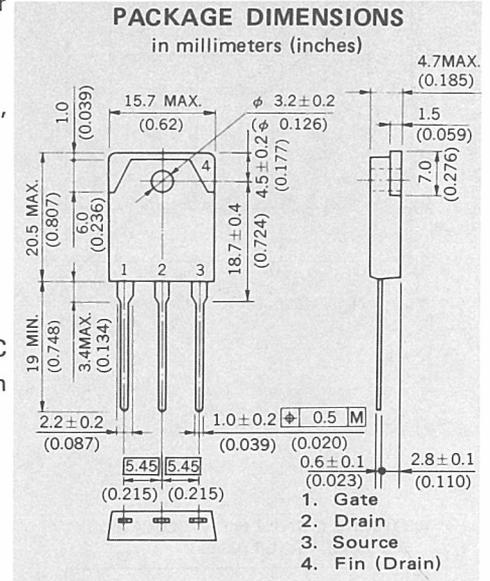
DESCRIPTION The 2SK875 is N-channel MOS Field Effect Power Transistor designed for switching power supplies DC-DC converters.

- FEATURES**
- Suitable for switching power supplied, actuator controls, and pulse circuits.
 - Low $R_{DS(on)}$
 - No second breakdown

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures	
Storage Temperature	-55 to +150 °C
Channel Temperature	150 °C Maximum
Maximum Power Dissipation ($T_C = 25\text{ °C}$)	
Total Power Dissipation	120 W
Maximum Voltages and Currents ($T_a = 25\text{ °C}$)	
V_{DSS} Drain to Source Voltage	450 V
V_{GSS} Gate to Source Voltage	±20 V
$I_{D(DC)}$ Drain Current (DC)	±12 A
$I_{D(pulse)}$ Drain Current (pulse)*	±48 A

* $PW \leq 100\ \mu s$, Duty Cycle $\leq 2\%$



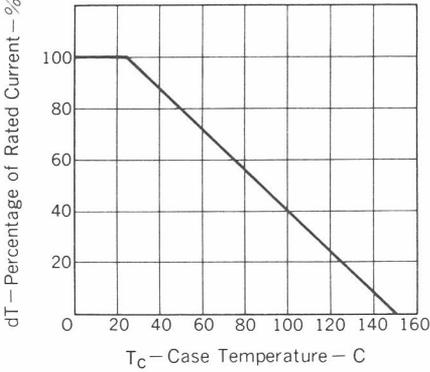
ELECTRICAL CHARACTERISTICS ($T_a = 25\text{ °C}$)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
I_{DSS}	Drain Leakage Current			100	μA	$V_{DS} = 450\text{ V}$, $V_{GS} = 0$
I_{GSS}	Gate to Source Leakage Current			±100	nA	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	1.5		3.5	V	$V_{DS} = 10\text{ V}$, $I_D = 1\text{ mA}$
$ Y_{fs} $	Forward Transfer Admittance	5.0			S	$V_{DS} = 10\text{ V}$, $I_D = 6\text{ A}$
$R_{DS(on)}$	Drain to Source On-State Resistance		0.5	0.60	Ω	$V_{GS} = 10\text{ V}$, $I_D = 6\text{ A}$
C_{iss}	Input Capacitance		2000		pF	$V_{DS} = 10\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$
C_{oss}	Output Capacitance		450		pF	
C_{rss}	Reverse Transfer Capacitance		120		pF	
$t_{d(on)}$	Turn-On Delay Time		30		ns	$I_D = 6\text{ A}$, $V_{DD} \doteq 150\text{ V}$ $V_{GS(on)} = 10\text{ V}$ $R_L = 25\ \Omega$ $R_{in} = 10\ \Omega$
t_r	Rise Time		50		ns	
$t_{d(off)}$	Turn-Off Delay Time		100		ns	
t_f	Fall Time		50		ns	

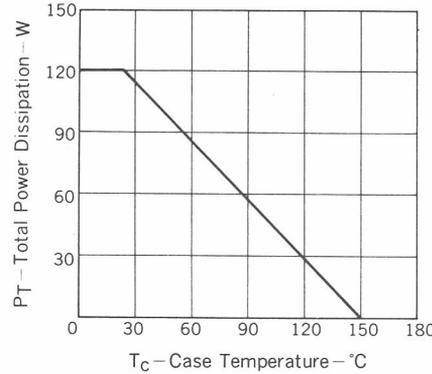
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TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

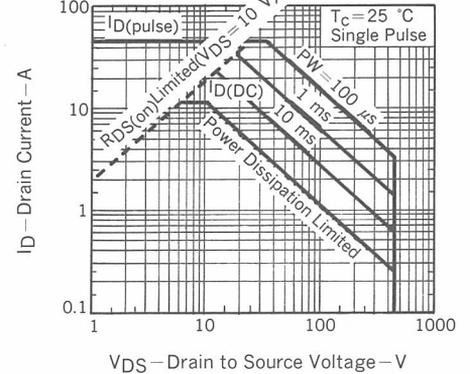
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



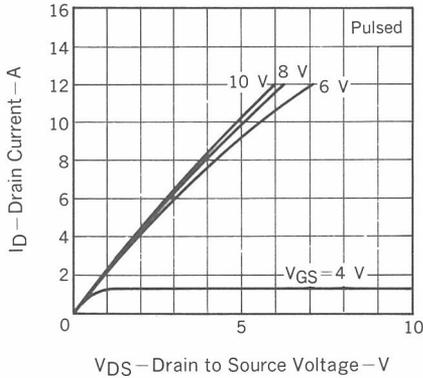
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



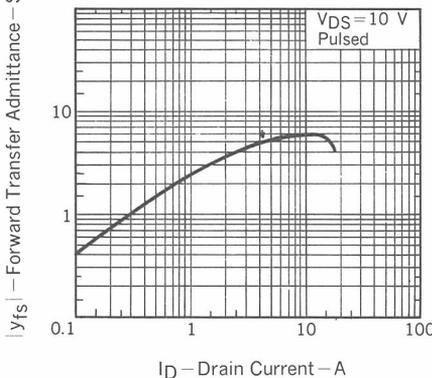
FORWARD BIAS SAFE OPERATING AREA



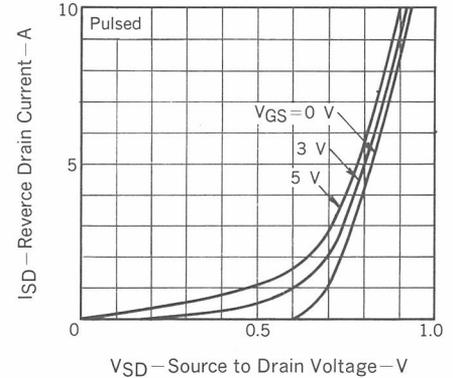
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



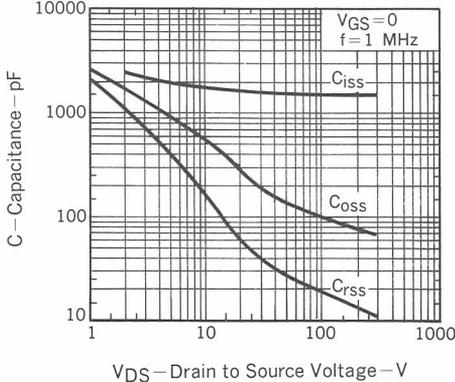
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



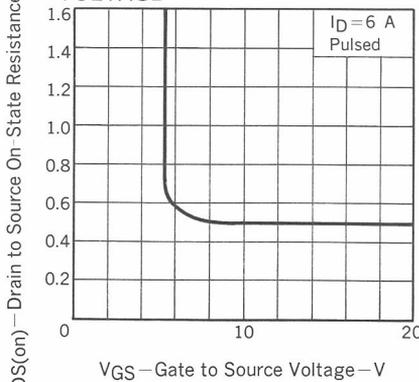
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



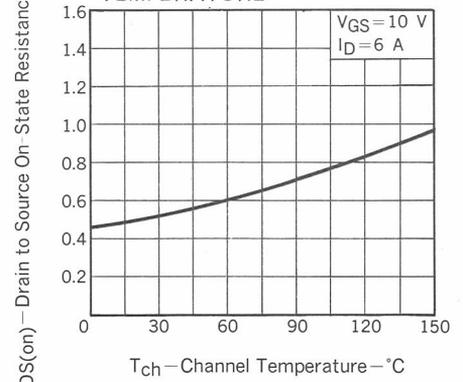
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



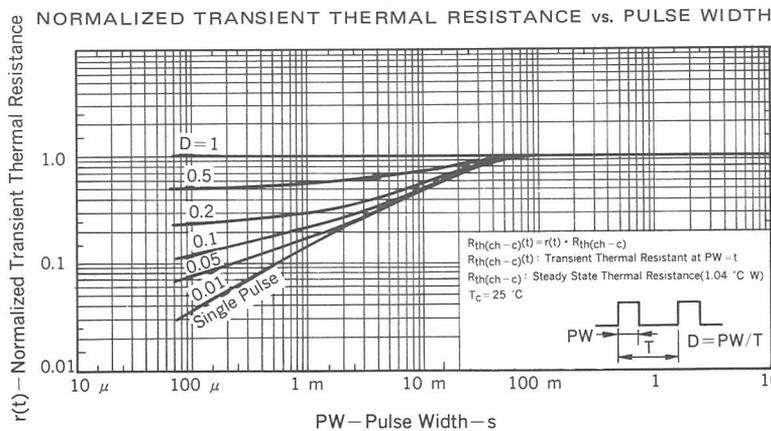
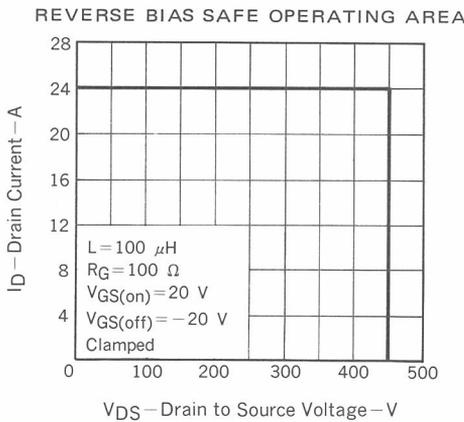
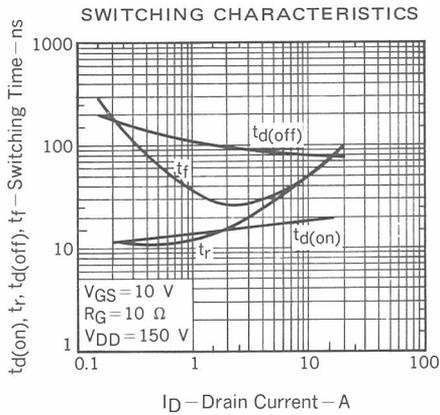
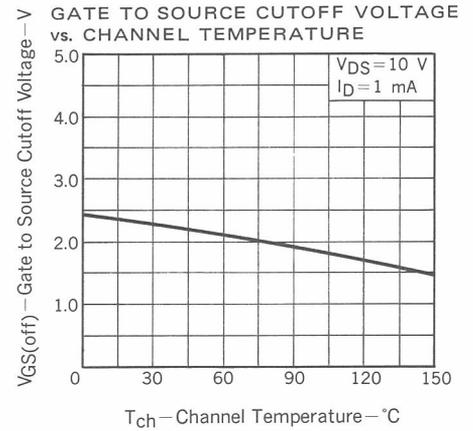
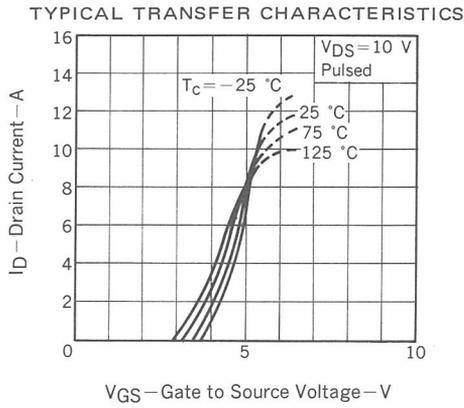
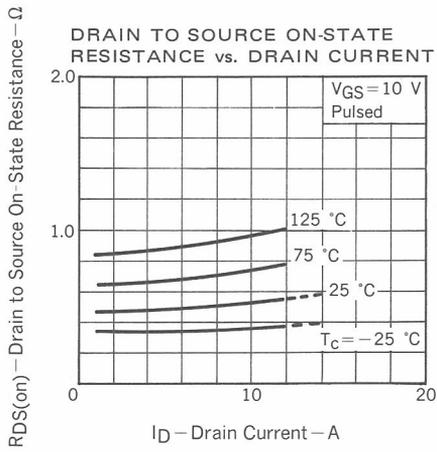
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

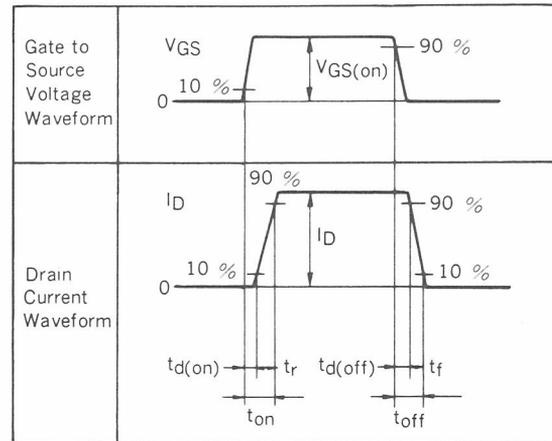
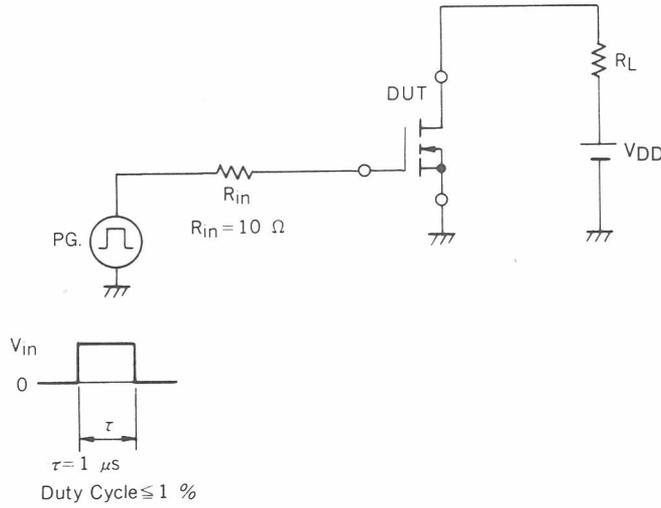


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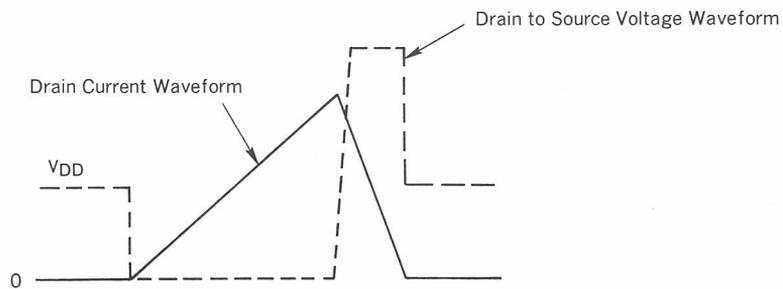
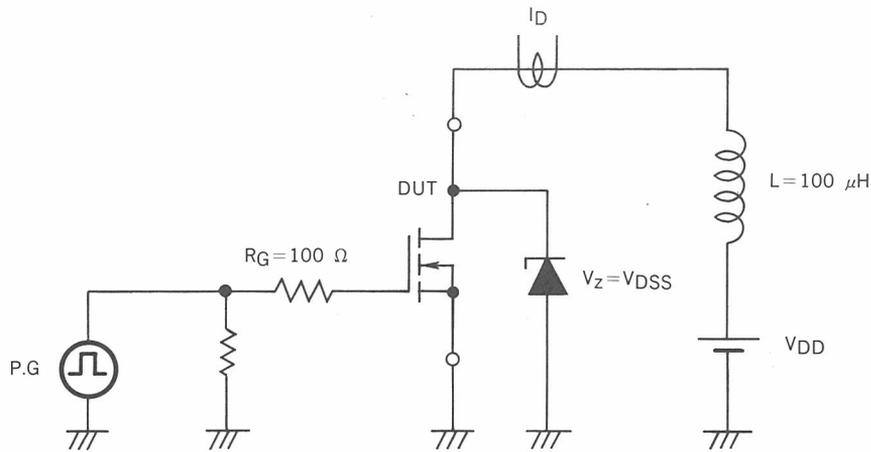


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SWITCHING TIME TEST CIRCUIT



CLAMPED INDUCTIVE TEST CIRCUIT



Clamped Inductive Waveforms